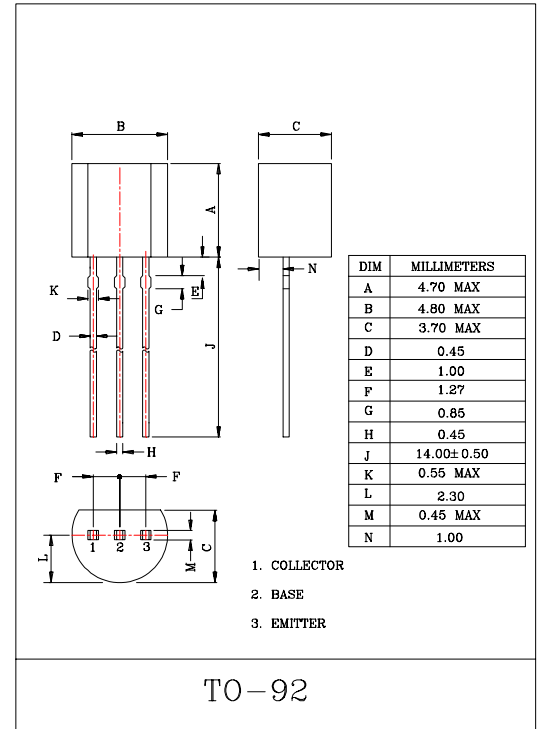


GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	500	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=0.1mA$	40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1.0mA$	10	-	-	V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=40V$	-	-	1.0	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=10V$	-	-	1.0	$\mu A$
DC Current Gain	$h_{FE}$	$I_C=100mA, V_{CE}=2V$	30k	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=1mA$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$	-	1.5	2.0	V
Current Gain Bandwidth Product	$f_T$	$I_C=100mA, V_{CE}=2V, f=100MHz$	-	220	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz$	-	5.0	-	pF

